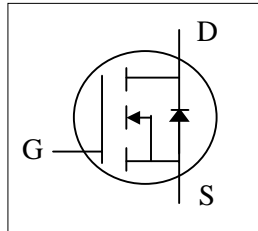




- ▼ Dynamic dv/dt Rating
- ▼ Repetitive Avalanche Rated
- ▼ Fast Switching
- ▼ Simple Drive Requirement

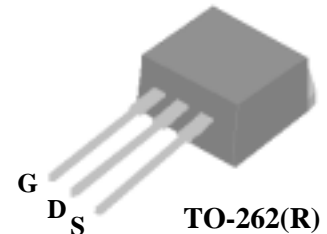
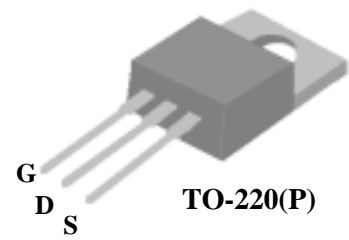


$BV_{DSS}$	600/675V
$R_{DS(ON)}$	0.75 $\Omega$
$I_D$	9A

### Description

AP09N70 series are specially designed as main switching devices for universal 90~265VAC off-line AC/DC converter applications. Both TO-220 and TO-262 type provide high blocking voltage to overcome voltage surge and sag in the toughest power system with the best combination of fast switching, ruggedized design and cost-effectiveness.

The TO-220 and TO-262 package is universally preferred for all commercial-industrial applications. The device is suited for switch mode power supplies, DC-AC converters and high current high speed switching circuits.



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage - /A	600/675	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D @ T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	9	A
$I_D @ T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	40	A
$P_D @ T_C=25^\circ C$	Total Power Dissipation	156	W
	Linear Derating Factor	1.25	W/ $^\circ C$
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	305	mJ
$I_{AR}$	Avalanche Current	9	A
$E_{AR}$	Repetitive Avalanche Energy	9	mJ
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Thermal Resistance Junction-case	Max. 0.8	$^\circ C/W$
Rthj-a	Thermal Resistance Junction-ambient	Max. 62	$^\circ C/W$


**Electrical Characteristics @ $T_j=25^\circ\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$ / -	600	-	-	V
		$V_{GS}=0V, I_D=1mA$ / A	675	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1mA$	-	0.6	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=4.5A$	-	-	0.75	$\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=4.5A$	-	4.5	-	S
$I_{DSS}$	Drain-Source Leakage Current ( $T_j=25^\circ\text{C}$ )	$V_{DS}=600V, V_{GS}=0V$	-	-	10	$\mu A$
	Drain-Source Leakage Current ( $T_j=150^\circ\text{C}$ )	$V_{DS}=480V, V_{GS}=0V$	-	-	100	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 30V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>3</sup>	$I_D=9A$	-	44	-	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=480V$	-	11	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	12	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>3</sup>	$V_{DD}=300V$	-	19	-	ns
$t_r$	Rise Time	$I_D=9A$	-	21	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=10\Omega, V_{GS}=10V$	-	56	-	ns
$t_f$	Fall Time	$R_D=34\Omega$	-	24	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	2660	-	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	170	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	10	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$I_S$	Continuous Source Current ( Body Diode )	$V_D=V_G=0V, V_S=1.5V$	-	-	9	A
$I_{SM}$	Pulsed Source Current ( Body Diode ) <sup>1</sup>		-	-	40	A
$V_{SD}$	Forward On Voltage <sup>3</sup>	$T_j=25^\circ\text{C}, I_S=9A, V_{GS}=0V$	-	-	1.5	V

**Notes:**

1. Pulse width limited by safe operating area.
2. Starting  $T_j=25^\circ\text{C}$ ,  $V_{DD}=50V$ ,  $L=6.8\text{mH}$ ,  $R_G=25\Omega$ ,  $I_{AS}=9A$ .
3. Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .

**Ordering Code**

 AP09N70P(/R)-X : X Denote  $BV_{DSS}$  Grade

 Blank =  $BV_{DSS}$  600V

 A =  $BV_{DSS}$  675V

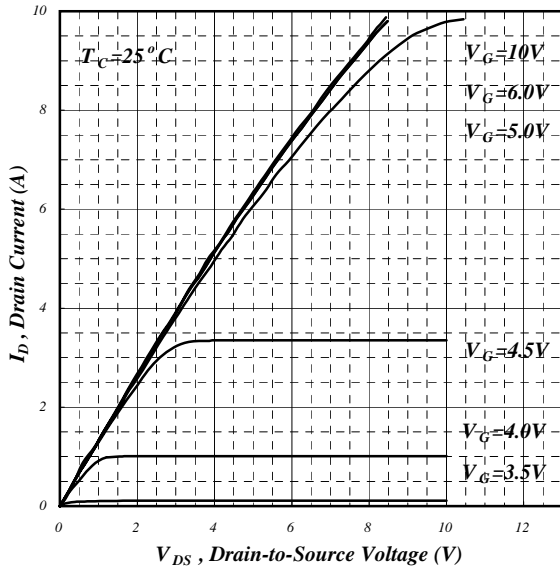


Fig 1. Typical Output Characteristics

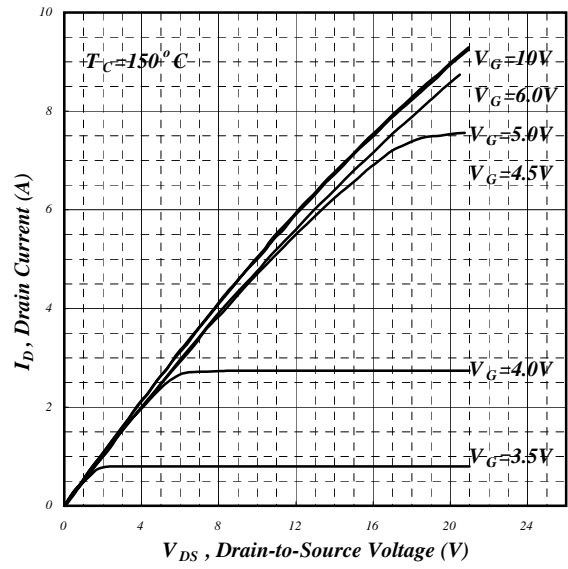


Fig 2. Typical Output Characteristics

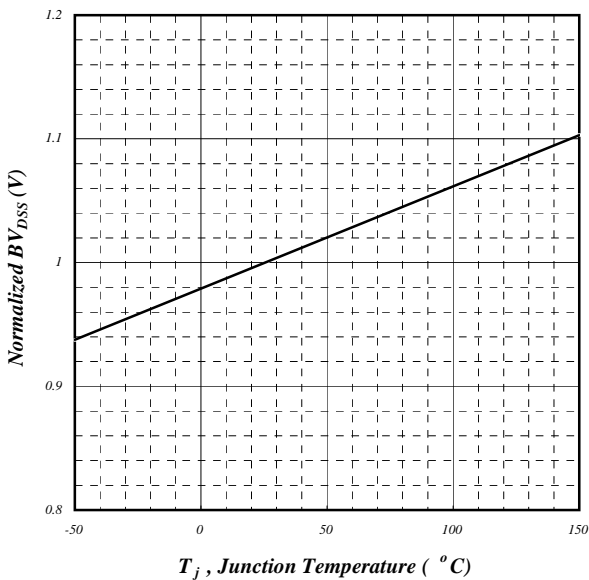


Fig 3. Normalized  $BV_{DSS}$  v.s. Junction Temperature

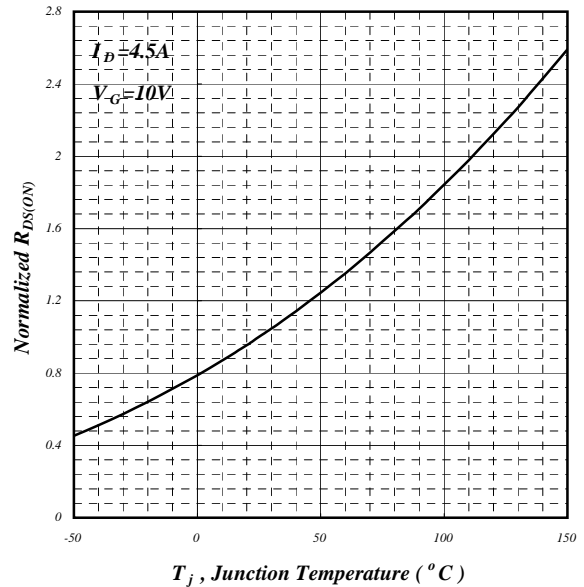


Fig 4. Normalized On-Resistance v.s. Junction Temperature

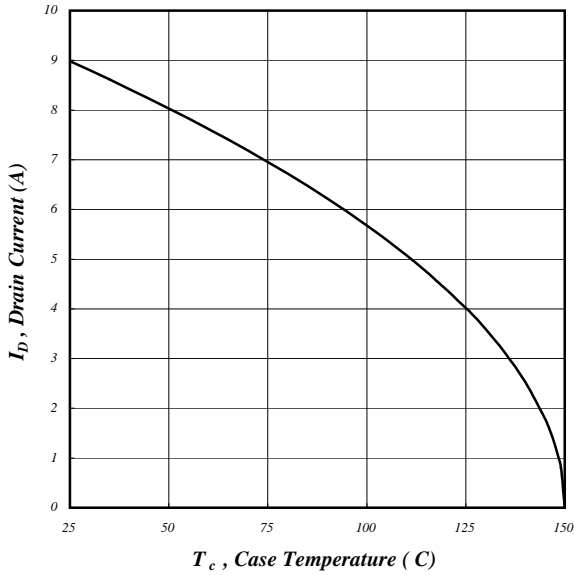


Fig 5. Maximum Drain Current v.s. Case Temperature

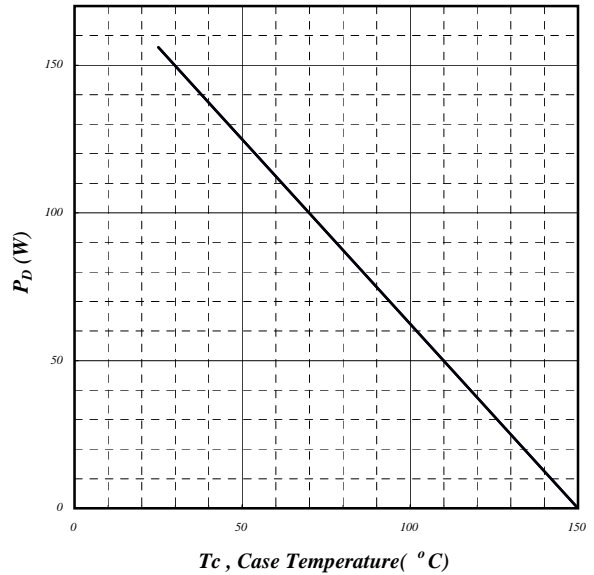


Fig 6. Typical Power Dissipation

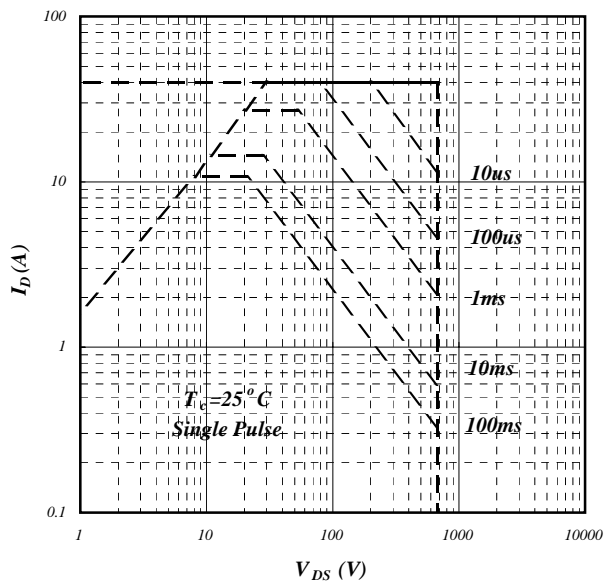


Fig 7. Maximum Safe Operating Area

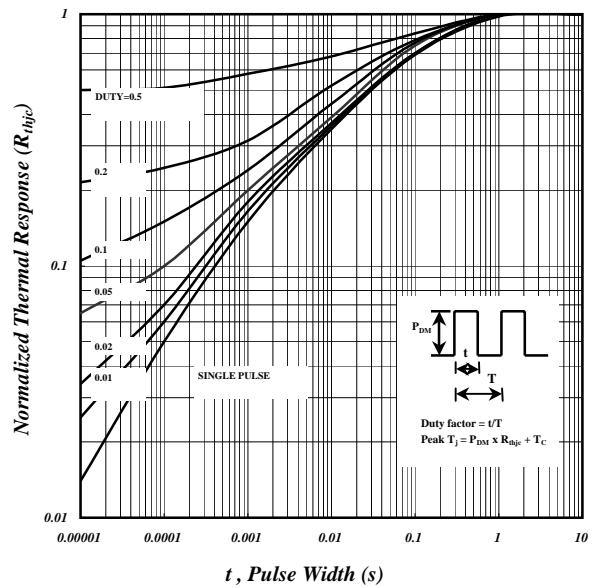


Fig 8. Effective Transient Thermal Impedance

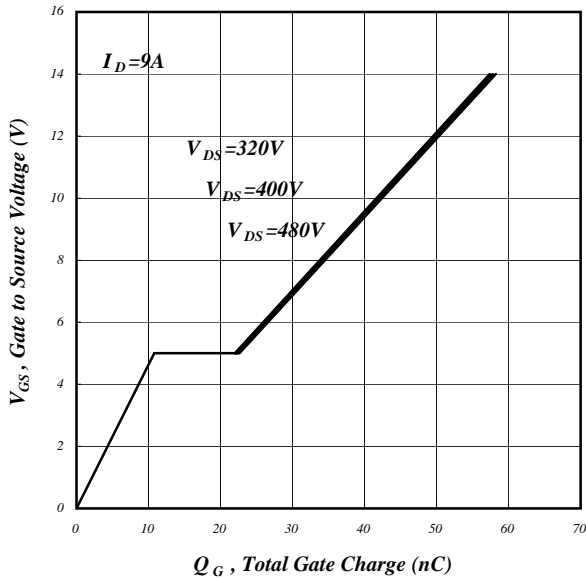


Fig 9. Gate Charge Characteristics

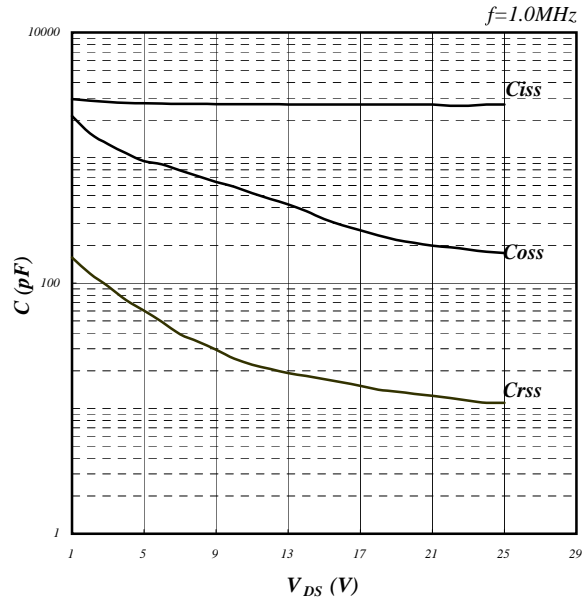


Fig 10. Typical Capacitance Characteristics

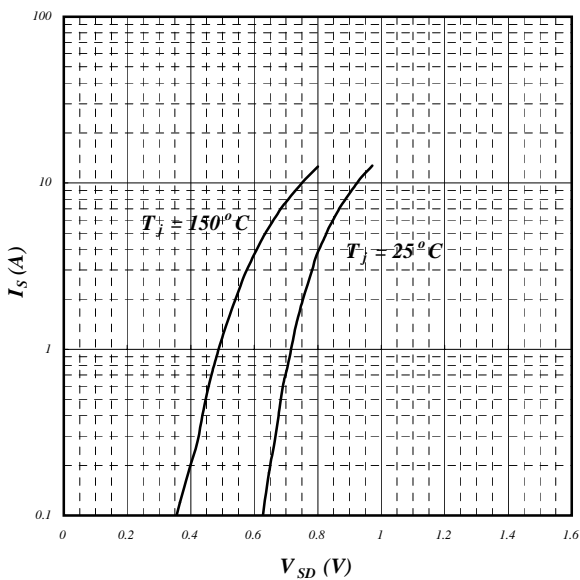


Fig 11. Forward Characteristic of Reverse Diode

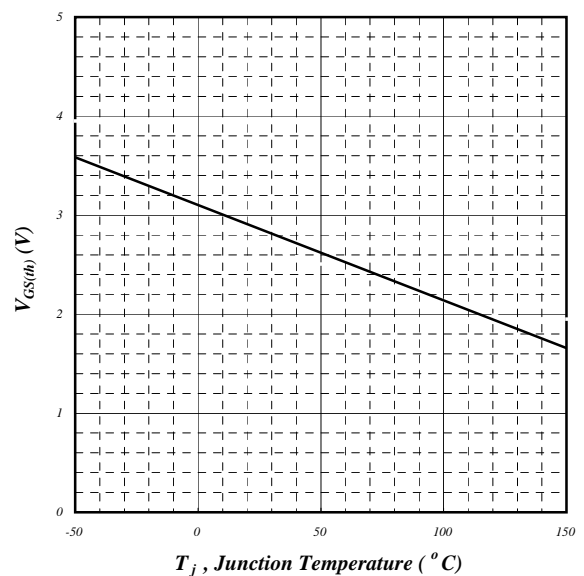


Fig 12. Gate Threshold Voltage v.s. Junction Temperature

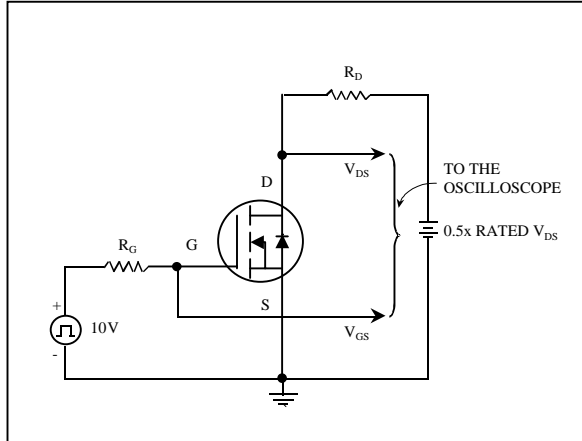


Fig 13. Switching Time Circuit

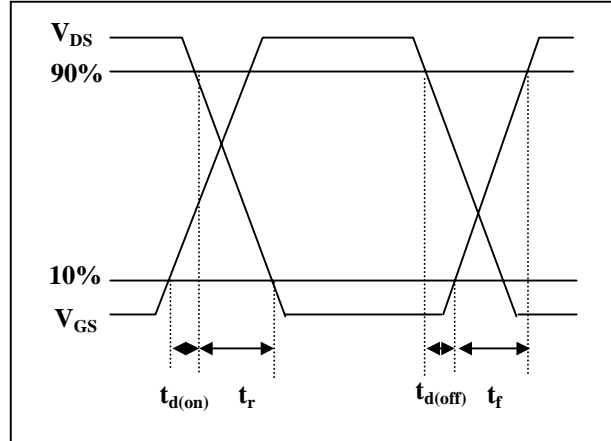


Fig 14. Switching Time Waveform

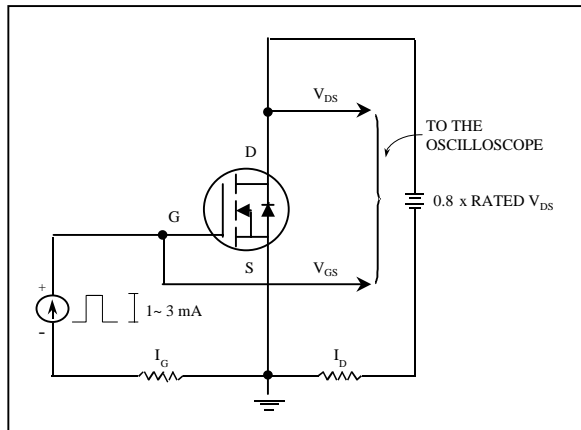


Fig 15. Gate Charge Circuit

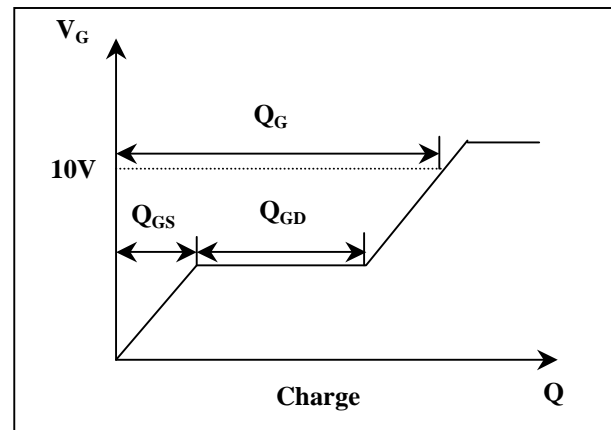


Fig 16. Gate Charge Waveform